

Silicon NPN Phototransistor

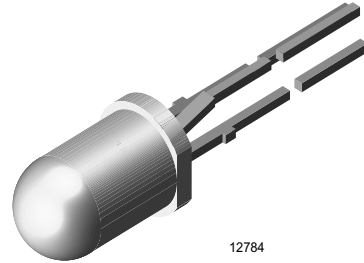
Description

BPV11F is a very high sensitive silicon NPN epitaxial planar phototransistor in a standard T-1 $\frac{3}{4}$ plastic package.

The epoxy package itself is an IR filter, spectrally matched to GaAs IR emitters ($\lambda_p \geq 900$ nm).

The viewing angle of $\pm 15^\circ$ makes it insensible to ambient straylight.

A base terminal is available to enable biasing and sensitivity control.



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Features

- Very high radiant sensitivity
- Standard T-1 $\frac{3}{4}$ (\varnothing 5 mm) package
- IR filter for GaAs emitters (950 nm)
- Angle of half sensitivity $\varphi = \pm 15^\circ$
- Base terminal available
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Applications

- Detector for industrial electronic circuitry, measurement and control

Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector Base Voltage		V_{CBO}	80	V
Collector Emitter Voltage		V_{CEO}	70	V
Emitter Base Voltage		V_{EBO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5$, $t_p \leq 10$ ms	I_{CM}	100	mA
Total Power Dissipation	$T_{amb} \leq 47^\circ\text{C}$	P_{tot}	150	mW
Junction Temperature		T_j	100	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 55 to + 100	$^\circ\text{C}$
Soldering Temperature	$t \leq 5$ s, 2 mm from body	T_{sd}	260	$^\circ\text{C}$
Thermal Resistance Junction/ Ambient		R_{thJA}	350	K/W

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector Emitter Breakdown Voltage	$I_C = 1\text{ mA}$	$V_{(BR)CEO}$	70			V
Collector-emitter dark current	$V_{CE} = 10\text{ V}, E = 0$	I_{CEO}		1	50	nA
DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 5\text{ mA}, E = 0$	h_{FE}		450		
Collector-emitter capacitance	$V_{CE} = 0\text{ V}, f = 1\text{ MHz}, E = 0$	C_{CEO}		15		pF
Collector - base capacitance	$V_{CB} = 0\text{ V}, f = 1\text{ MHz}, E = 0$	C_{CBO}		19		pF

Optical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector Light Current	$E_e = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, V_{CE} = 5\text{ V}$	I_{ca}	3	9		mA
Angle of Half Sensitivity		ϕ		± 15		deg
Wavelength of Peak Sensitivity		λ_p		930		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		900 to 980		nm
Collector Emitter Saturation Voltage	$E_e = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, I_C = 1\text{ mA}$	V_{CEsat}		130	300	mV
Turn-On Time	$V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\text{ }\Omega$	t_{on}		6		μs
Turn-Off Time	$V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\text{ }\Omega$	t_{off}		5		μs
Cut-Off Frequency	$V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\text{ }\Omega$	f_c		110		kHz

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

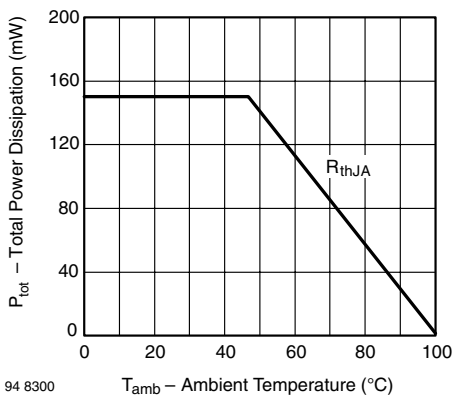


Figure 1. Total Power Dissipation vs. Ambient Temperature

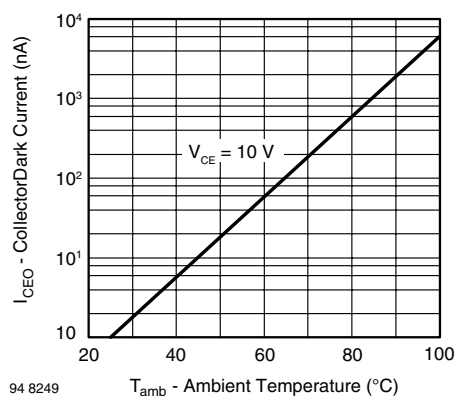


Figure 2. Collector Dark Current vs. Ambient Temperature

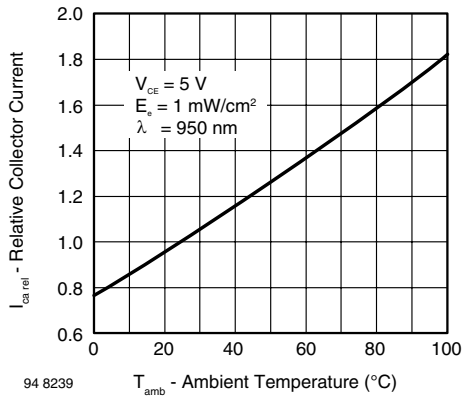


Figure 3. Relative Collector Current vs. Ambient Temperature

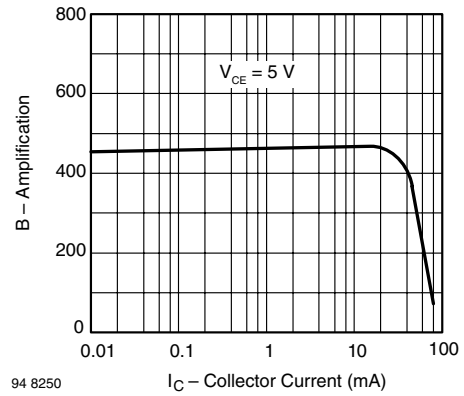


Figure 6. Amplification vs. Collector Current

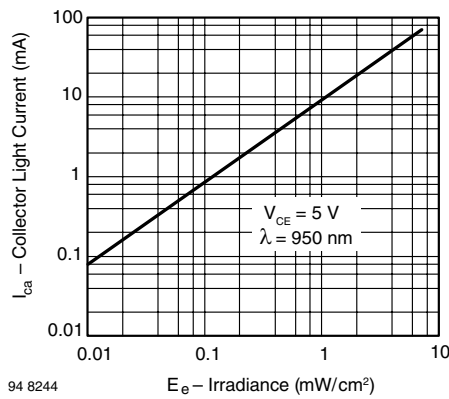


Figure 4. Collector Light Current vs. Irradiance

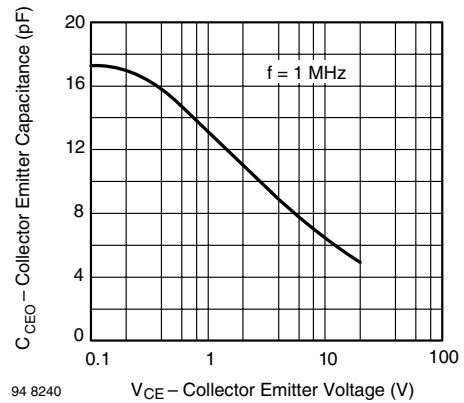


Figure 7. Collector Base Capacitance vs. Collector Base Voltage

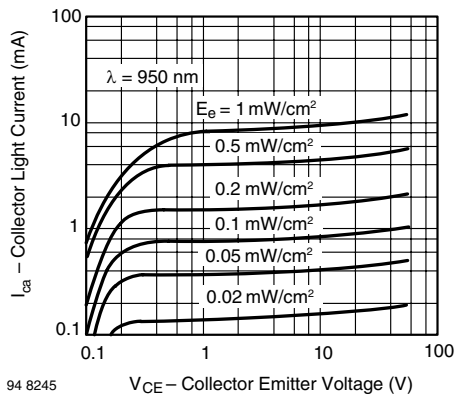


Figure 5. Collector Light Current vs. Collector Emitter Voltage

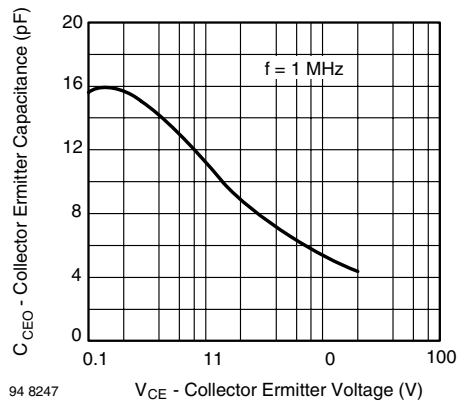
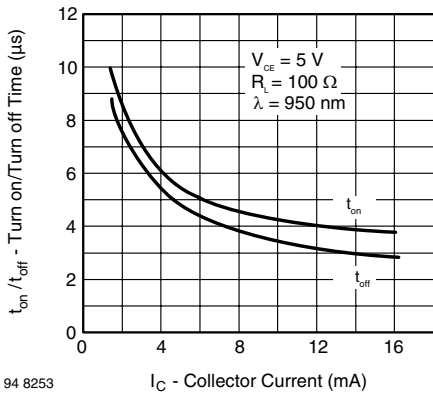
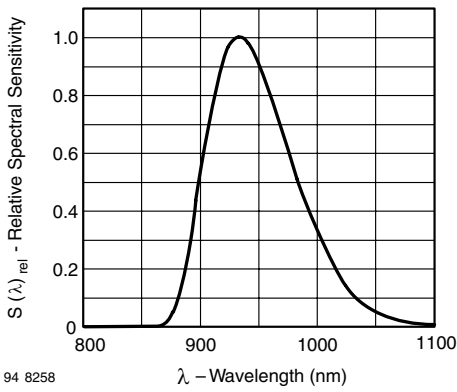


Figure 8. Collector Emitter Capacitance vs. Collector Emitter Voltage



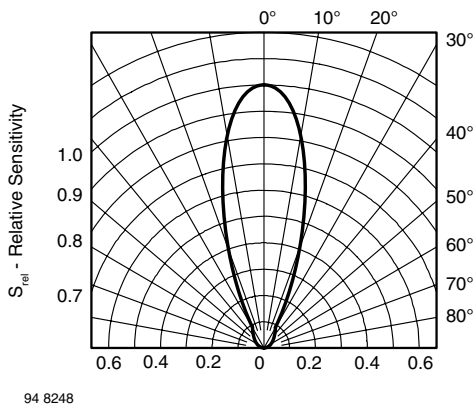
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Figure 9. Turn On/Turn Off Time vs. Collector Current



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Figure 10. Relative Spectral Sensitivity vs. Wavelength



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Figure 11. Relative Radiant Sensitivity vs. Angular Displacement

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1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

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